

Title (en)
SEMICONDUCTOR DEVICE AND STRUCTURE

Title (de)
HALBLEITERVORRICHTUNG UND STRUKTUR DAMIT

Title (fr)
DISPOSITIF À SEMI-CONDUCTEURS, ET STRUCTURE ASSOCIÉE

Publication
EP 2599112 A2 20130605 (EN)

Application
EP 11812914 A 20110628

Priority

- US 201113041405 A 20110306
- US 201113041406 A 20110306
- US 201113016313 A 20110128
- US 97060210 A 20101216
- US 95192410 A 20101122
- US 95191310 A 20101122
- US 94961710 A 20101118
- US 94107510 A 20101107
- US 94107410 A 20101107
- US 94107310 A 20101107
- US 90410810 A 20101013
- US 90411910 A 20101013
- US 90189010 A 20101011
- US 90037910 A 20101007
- US 89425210 A 20100930
- US 85966510 A 20100819
- US 84927210 A 20100803
- US 84791110 A 20100730
- US 2011042071 W 20110628

Abstract (en)
[origin: WO2012015550A2] A method for fabrication of semiconductor device comprising a first wafer comprising first single crystal layer comprising first transistors, first alignment marks, and first transistors interconnect layers comprising at least one metal layer overlying said first single crystal silicon layer, wherein said at least one metal layer comprises copper or aluminum; and comprising a step of implant and high temperature activation to form a conductive layer within a second wafer; and forming a second crystallized layer on top of said first wafer by transferring said conductive layer using ion-cut process, and forming second transistors on said second crystallized layer wherein said second transistors source and drain comprises portion of said first conductive layer.

IPC 8 full level
H01L 21/336 (2006.01); **H01L 21/8238** (2006.01); **H01L 27/092** (2006.01); **H01L 29/78** (2006.01); **H10B 41/20** (2023.01); **H10B 41/35** (2023.01); **H10B 41/41** (2023.01); **H10B 43/20** (2023.01)

CPC (source: EP)
B82Y 10/00 (2013.01); **H01L 21/6835** (2013.01); **H01L 21/743** (2013.01); **H01L 21/76254** (2013.01); **H01L 21/845** (2013.01); **H01L 22/22** (2013.01); **H01L 23/481** (2013.01); **H01L 23/5252** (2013.01); **H01L 27/0207** (2013.01); **H01L 27/0688** (2013.01); **H01L 27/11803** (2013.01); **H01L 27/1211** (2013.01); **H01L 29/165** (2013.01); **H01L 29/42392** (2013.01); **H01L 29/66439** (2013.01); **H01L 29/775** (2013.01); **H01L 29/7841** (2013.01); **H01L 29/7881** (2013.01); **H01L 29/792** (2013.01); **H10B 10/00** (2023.02); **H10B 10/125** (2023.02); **H10B 12/20** (2023.02); **H10B 41/20** (2023.02); **H10B 41/35** (2023.02); **H10B 41/41** (2023.02); **H10B 43/20** (2023.02); **G11C 29/32** (2013.01); **G11C 2029/3202** (2013.01); **H01L 2221/68327** (2013.01); **H01L 2221/68381** (2013.01); **H01L 2224/131** (2013.01); **H01L 2224/16145** (2013.01); **H01L 2224/16225** (2013.01); **H01L 2224/16227** (2013.01); **H01L 2224/32145** (2013.01); **H01L 2224/32225** (2013.01); **H01L 2224/73153** (2013.01); **H01L 2224/73204** (2013.01); **H01L 2224/73253** (2013.01); **H01L 2224/73265** (2013.01); **H01L 2224/81801** (2013.01); **H01L 2224/83005** (2013.01); **H01L 2224/83896** (2013.01); **H01L 2224/92242** (2013.01); **H01L 2924/01019** (2013.01); **H01L 2924/01066** (2013.01); **H01L 2924/01067** (2013.01); **H01L 2924/10253** (2013.01); **H01L 2924/12032** (2013.01); **H01L 2924/1305** (2013.01); **H01L 2924/13062** (2013.01); **H01L 2924/13091** (2013.01); **H01L 2924/14** (2013.01); **H01L 2924/1461** (2013.01); **H01L 2924/15311** (2013.01); **H10B 12/056** (2023.02); **H10B 12/36** (2023.02); **H10B 41/40** (2023.02); **H10B 43/40** (2023.02); **H10B 63/30** (2023.02); **H10B 63/845** (2023.02); **H10N 70/20** (2023.02); **H10N 70/823** (2023.02); **H10N 70/8833** (2023.02)

C-Set (source: EP)
1. **H01L 2224/81801 + H01L 2924/00014**
2. **H01L 2224/131 + H01L 2924/014**
3. **H01L 2924/10253 + H01L 2924/00**
4. **H01L 2224/73204 + H01L 2224/16145 + H01L 2224/32145 + H01L 2924/00**
5. **H01L 2924/1461 + H01L 2924/00**
6. **H01L 2924/12032 + H01L 2924/00**
7. **H01L 2924/1305 + H01L 2924/00**
8. **H01L 2924/13062 + H01L 2924/00**
9. **H01L 2224/73204 + H01L 2224/16225 + H01L 2224/32225 + H01L 2924/00**
10. **H01L 2924/15311 + H01L 2224/73204 + H01L 2224/16225 + H01L 2224/32225 + H01L 2924/00**

Designated contracting state (EPC)
AL AT BE BG CH CY CZ DE DK EE ES FI FR GB GR HR HU IE IS IT LI LT LU LV MC MK MT NL NO PL PT RO RS SE SI SK SM TR

DOCDB simple family (publication)
WO 2012015550 A2 20120202; WO 2012015550 A3 20120419; WO 2012015550 A9 20120531; EP 2599112 A2 20130605; EP 2599112 A4 20170726; EP 3460845 A1 20190327

DOCDB simple family (application)

